PROCESS CPZ28

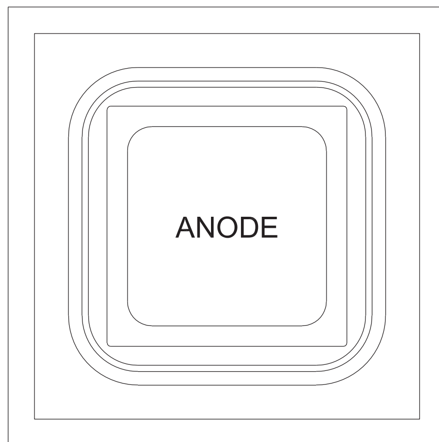
Zener Diode

0.5 Watt Zener Diode Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	13 x 13 MILS
Die Thickness	7.8 MILS
Anode Bonding Pad Area	7.0 x 7.0 MILS
Top Side Metalization	Ti/Al - 13,000Å
Back Side Metalization	Au-As - 13,000Å

GEOMETRY



R0

BACKSIDE CATHODE

GROSS DIE PER 5 INCH WAFER
101,184

PRINCIPAL DEVICE TYPES
CMPZ5221B
THRU
CMPZ5267B

R2 (22-March 2010)

PROCESS CPZ28

Typical Electrical Characteristics